## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Geoff W. Taylor et al.

Group Art Unit:

Examiner:

Serial No.: 10/627,043

,043

Filed: July 25, 2003

Attorney Docket:OPE-023

Title: Semiconductor Laser Array Device Employing Modulation Doped Quantum Well

Structures

I hereby certify that this correspondence is being deposited on this day with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, Alexandria, VA 22313-1450.

David P Gordon

Date

Honorable Commissioner for Patents Alexandria, VA 22313

## SUBMITTAL OF DOCUMENTS PURSUANT TO DUTY OF DISCLOSURE

Pursuant to applicant's duty of disclosure 37 CFR Section 1.56, enclosed is a completed form PTOL-1449 as well as copies of the cited documents that relate to the above-referenced patent application. Since this document submittal is being presented prior to the first examination on the merits, no fee is due herewith.

The listed documents are brought to the Examiner's attention because they are known to the applicant and/or the applicant's attorney and may be considered by the Examiner to be material to his/her examination. This listing should not be construed as representation that a search has been made or that no better art exists. No inference should be made that the documents are in fact material merely because they are referenced herein. Moreover, no representation is made that the brief descriptions of the references herein necessarily describe the most material aspects of the references. Further, by this listing, the applicant is not making any admission regarding the relative dates of the invention and listed disclosures.

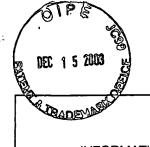
Respectfully submitted,

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## INFORMATION DISCLOSURE CITATION

Atty Docket No. OPE-023

Serial No. 10/627,043

Applicant

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## US PATENT DOCUMENTS

Examiner Initials		Document No.	Date	Name	Class	Subclass Filing date if approp.
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	E	4,806,997	2/21/89	Simmons et al.	357	16
	F	4,814,774	3/21/89	Herczfeld	342	372
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EXAMINER	EXAMINER			DATE CONSIDERED		

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	ВВ	10-Gbit/s InP-Based High-Performance Monolithic Photoreceivers Consisting p-i-n Photodiodes and HEMT's by Kiyoto Takahata et al., IEICE TRANS. ELECTRO Vol. E83-C, No. 6, June 2000					
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-	DD	20 Gbit/s Long Wavelength Monolithic Integrated Photoreceiver Grown on GaAV. Hurm et al., Electronic Letters, Vol. 33, No. 7, 27 March 1997					
	Æ	Heterojunction Field-Effect Transistor (HFET) by G.W. Taylor et al., Electronics Letters, Vol. 22, No. 15, pp. 784-786, 17 July 1986					
	FF	High Temperature Annealing of Modulation Doped GaAs/A1GaAs Heterostructures for FET Applications by H. Lee et al., 1983 IEEE/Cornell Conf. On High-Speed Semiconductor Devices & Ckts, 8/83					
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